

PMGD780SN

Dual N-channel μTrenchMOS standard level FET

Rev. 02 — 19 April 2010 Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode field-effect transistor in a small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using TrenchMOS technology.

1.2 Features and benefits

- Surface-mounted package
- Standard level threshold voltage
- Low on-state resistance
- Footprint 40 % smaller than SOT23
- Fast switching
- Dual device

1.3 Applications

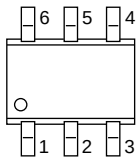
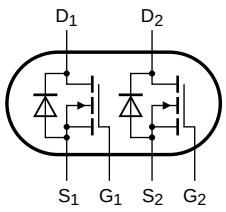
- Driver circuits
- Switching in portable appliances

1.4 Quick reference data

- $V_{DS} \leq 60$ V
- $P_{tot} \leq 0.41$ W
- $I_D \leq 0.49$ A
- $R_{DSon} \leq 920$ mΩ

2. Pinning information

Table 1. Pinning - SOT363 (SC-88), simplified outline and symbol

Pin	Description	Simplified outline	Graphic symbol
1	source1 (S1)	 SOT363 (SC-88)	
2	gate1 (G1)		
3	drain2 (D2)		
4	source2 (S2)		
5	gate2 (G2)		
6	drain1 (D1)		

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
PMGD780SN	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Limiting values

Table 3. Limiting values

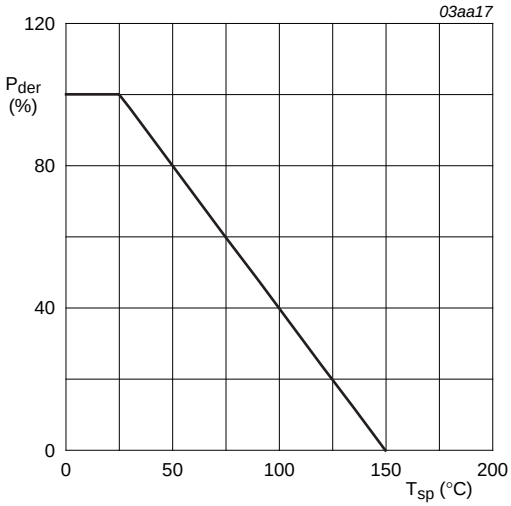
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 150 °C		-	60	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 kΩ		-	60	V
V_{GS}	gate-source voltage			-	±20	V
I_D	drain current	T_{sp} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	[1]	-	0.49	A
		T_{sp} = 100 °C; V_{GS} = 10 V; Figure 2	[1]	-	0.31	A
I_{DM}	peak drain current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 μs; Figure 3	[1]	-	0.99	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; Figure 1		-	0.41	W
T_{stg}	storage temperature			−55	+150	°C
T_j	junction temperature			−55	+150	°C
Source-drain diode						
I_S	source current	T_{sp} = 25 °C	[1]	-	0.34	A
I_{SM}	peak source current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 μs	[1]	-	0.69	A

[1] Single device conducting.

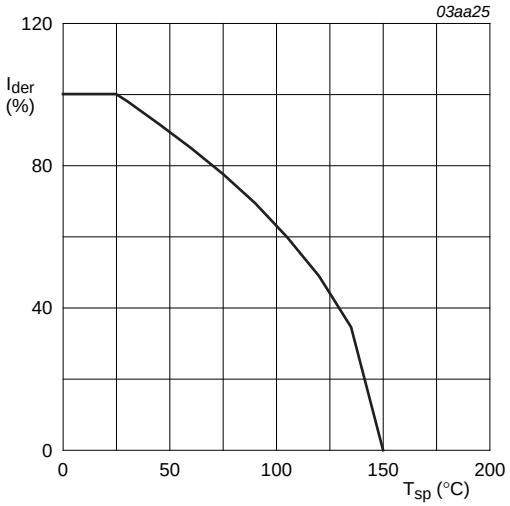
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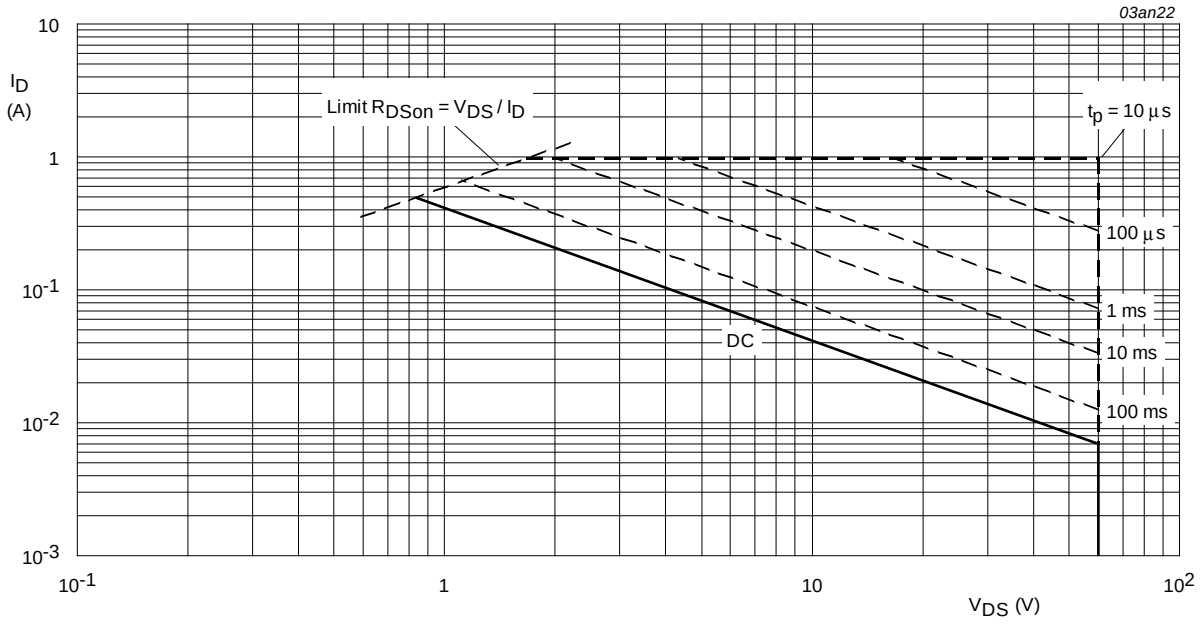
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature



T_{sp} = 25 °C; I_{DM} is single pulse; V_{GS} = 10 V

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Figure 4	-	-	300	K/W

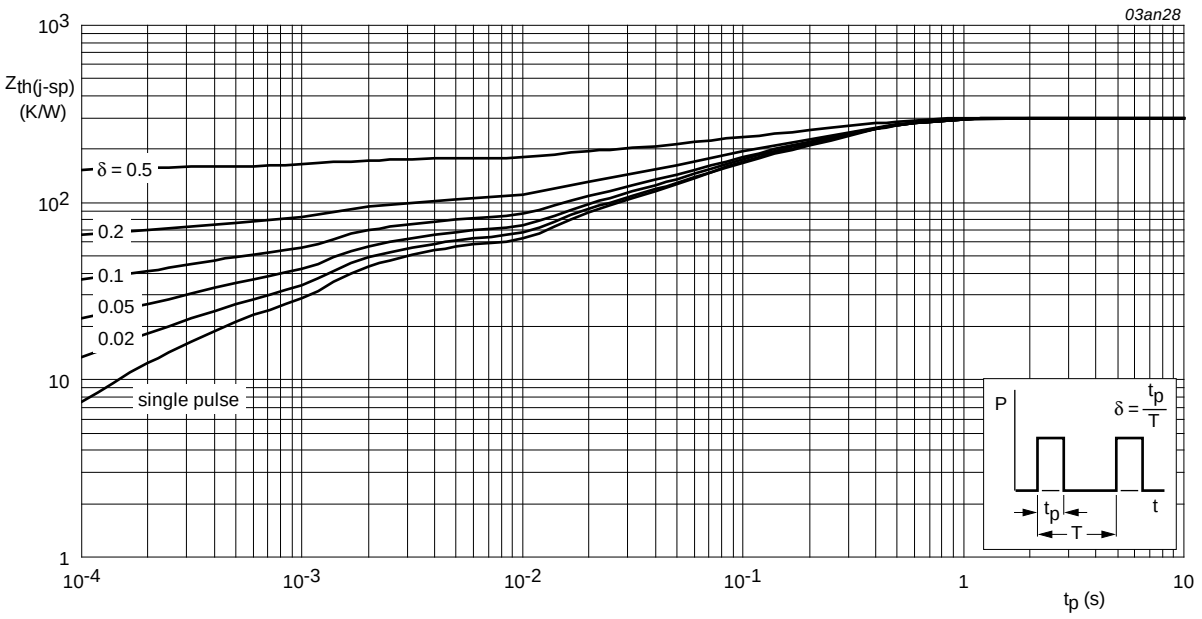


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

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6. Characteristics

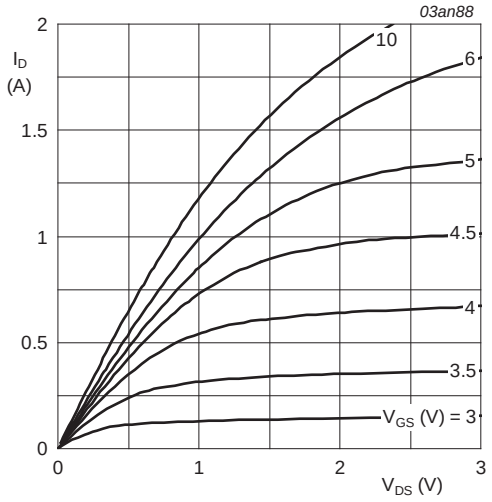
Table 5. Characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μA; V_{GS} = 0 V				
		T_j = 25 °C	60	-	-	V
		T_j = −55 °C	55	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 0.25 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	1	2	2.5	V
		T_j = 150 °C	0.6	–	–	V
		T_j = −55 °C	–	–	3.5	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.05	1	μA
		T_j = 150 °C	-	-	100	μA
I_{GSS}	gate leakage current	V_{GS} = ±20 V; V_{DS} = 0 V	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 0.3 A; Figure 7 and 8				
		T_j = 25 °C	-	780	920	mΩ
		T_j = 150 °C	-	1445	1700	mΩ
		V_{GS} = 4.5 V; I_D = 0.075 A; Figure 7 and 8	-	1100	1400	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 1 A; V_{DD} = 30 V; V_{GS} = 10 V; Figure 13	-	1.05	-	nC
Q_{GS}	gate-source charge		-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.22	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 30 V; f = 1 MHz; Figure 11	-	23	-	pF
C_{oss}	output capacitance		-	5	-	pF
C_{rss}	reverse transfer capacitance		-	3.5	-	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 30 V; R_L = 30 Ω; V_{GS} = 10 V; R_G = 6 Ω	-	2	-	ns
t_r	rise time		-	4	-	ns
$t_{d(off)}$	turn-off delay time		-	5	-	ns
t_f	fall time		-	2.2	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 0.3 A; V_{GS} = 0 V; Figure 12	-	0.83	1.2	V

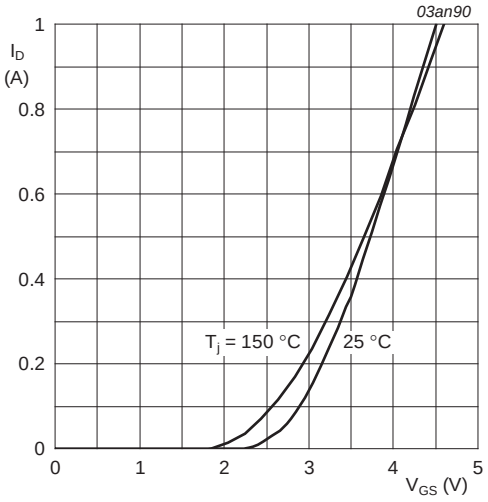
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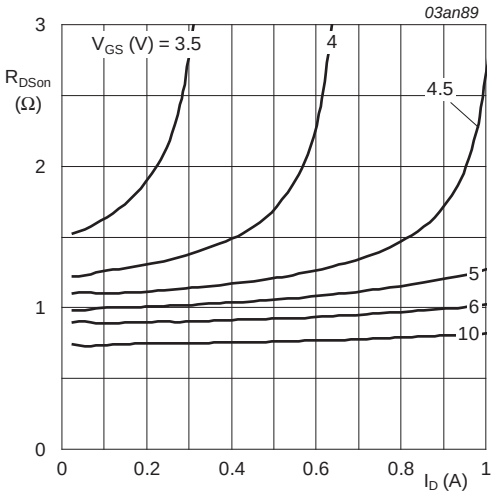
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



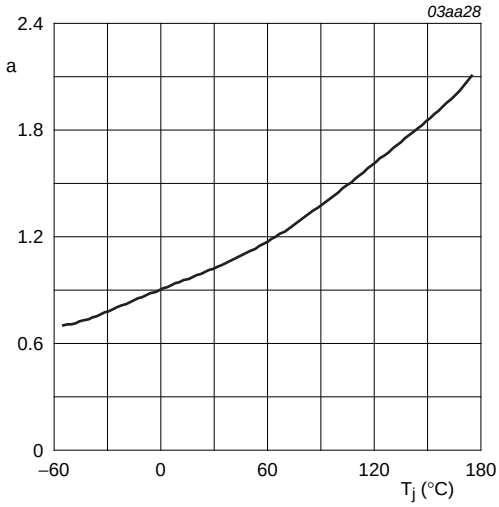
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values

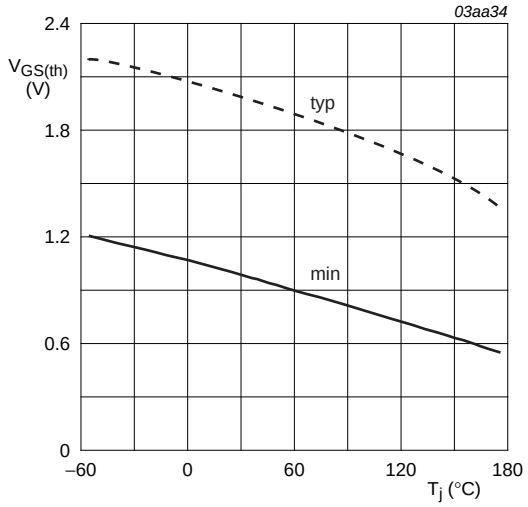


$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

Fig 8. Normalized drain-source on-state resistance as a function of junction temperature

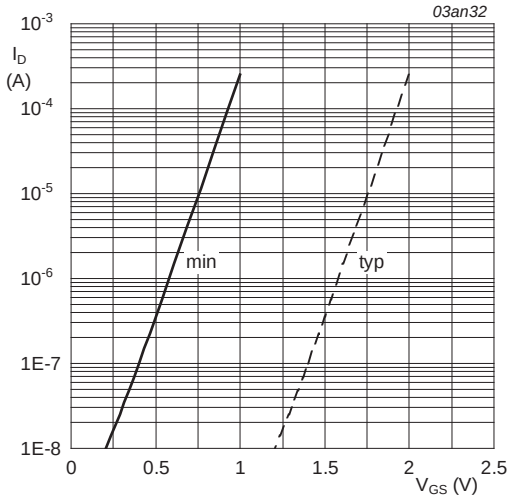
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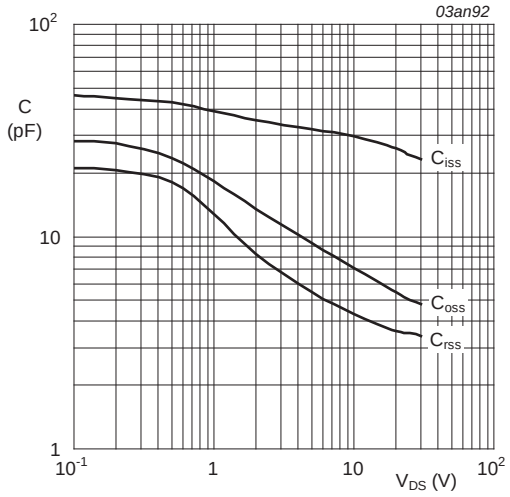
I_D = 0.25 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature



T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage

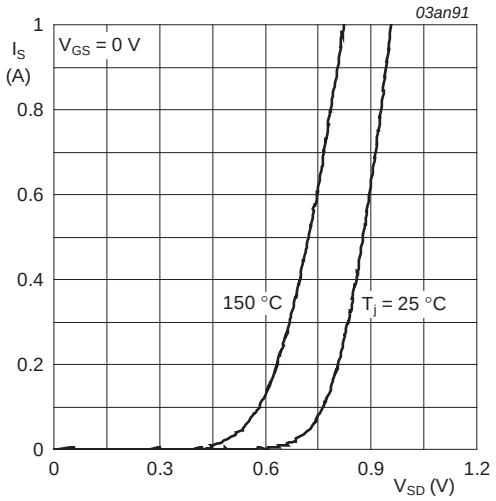


V_{GS} = 0 V; f = 1 MHz

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

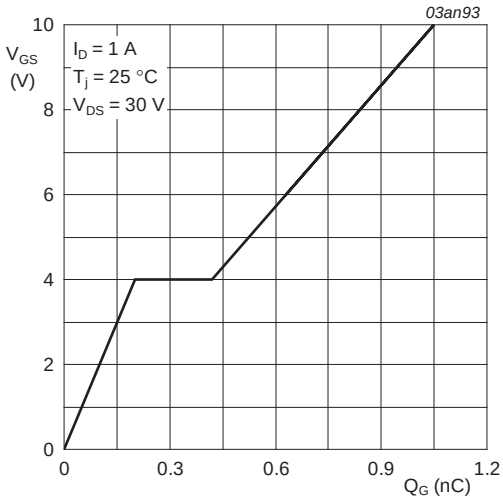
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T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 12. Source current as a function of source-drain voltage; typical values



I_D = 1 A; V_{DD} = 30 V

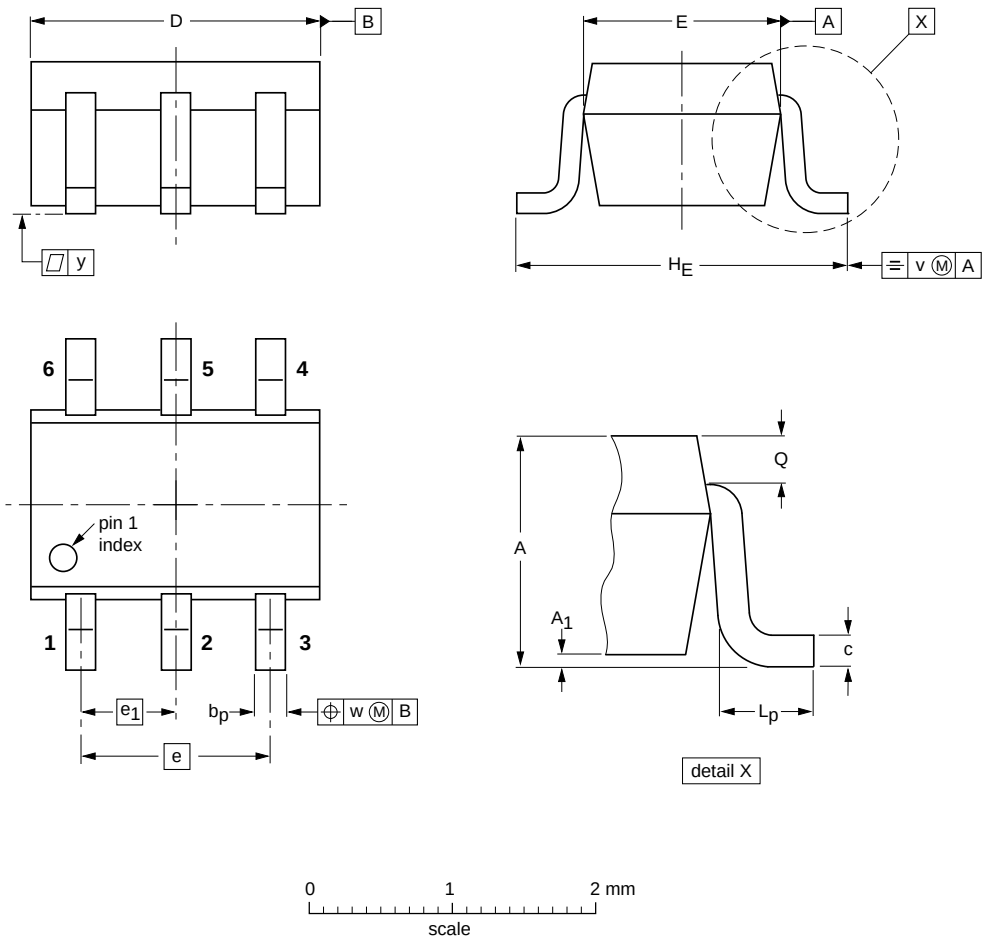
Fig 13. Gate-source voltage as a function of gate charge; typical values

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7. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 14. Package outline SOT363 (SC-88)

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8. Soldering

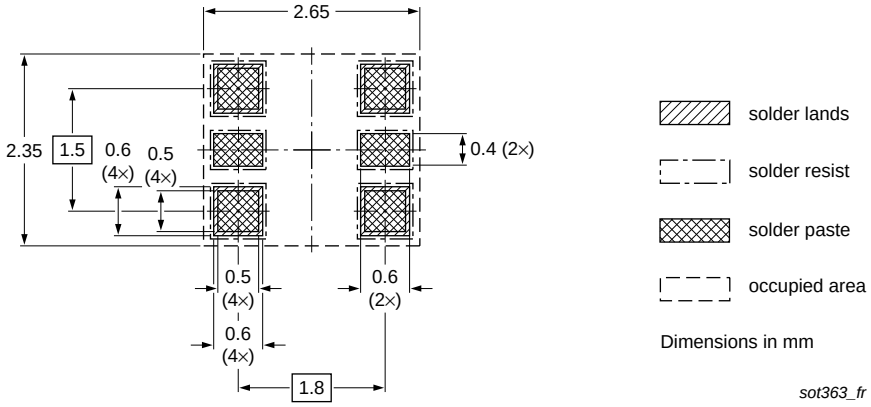


Fig 15. Reflow soldering footprint SOT363 (SC-88)

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9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMGD780SN_2	20100419	Product data sheet	-	PMGD780SN_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 5 “Characteristics”: added $V_{GS(th)}$ maximum value at condition T_j = 25 °C • Section 10 “Legal information”: updated			
PMGD780SN_1	20040211	Product data	-	-

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10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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